

5

In the Claims

Amendments to the Claims:

1. (currently amended) A die, comprising:

a substrate; and

one or more pillar structures formed over the substrate in a pattern; at least one of the one or more pillar structures <u>are bi-layer</u> having a lower lead-free portion and a coextensive upper solder material portion.

- 2. (original) The die of claim 1, wherein the one or more pillar structures have a rectangular shape, a round shape, a ring shape, a wall-like shape or a spline shape.
- 3. (original) The die of claim 1, wherein the one or more pillar structures have a rectangular shape with a length of from about 789.0 to 1289.0 μ m and a width of about 289.0 μ m.
- 4. (original) The die of claim 1, wherein the one or more pillar structures have a rectangular shape with a length of about $789.0 \, \mu m$ and a width of about $289.0 \, \mu m$.

S/N: 10/682,054

5. (original) The die of claim 1, wherein the one or more pillar structures have a

rectangular shape with a length of about 1289.0 µm and a width of about 289.0 µm.

6. (original) The die of claim 1, wherein the one or more pillar structures have a

rectangular shape and the pillar structures are spaced apart lengthwise by about

500.0 μm center-to-center and by about 211.0 μm end-to-end.

7. (original) The die of claim 1, wherein the one or more pillar structures have a

round shape with a diameter of about 289.0 µm.

8. (original) The die of claim 1, wherein the one or more pillar structures have a

round shape with a diameter of about 289.0 µm; the pillar structures being arranged

at least in part in rows and columns with the adjacent round pillar structures being

spaced apart by about 500.0 µm.

9. (original) The die of claim 1, wherein the pillar structure pattern includes a series

of rows and columns.

10. (previously presented) The die of claim 1, wherein the pillar structure pattern

includes a series of rows and columns; the pillar structures arranged in the series of

Docket: APS 03 - 002 S/N: 10/682,054
rows and columns are spaced apart lengthwise by about 500.0 µm center-to-center
in the columns and are spaced apart about 211.0 μm end-to-end.
11 (original) The die of claim 1 subgrain the one surrous village tweet with 1 1 4
11. (original) The die of claim 1, wherein the one or more pillar structures include at least one wall-shaped pillar structure.
·
12. (original) The die of claim 1, wherein the one or more pillar structures include at
least one wall-shaped pillar structure forming a square.
13. (original) The die of claim 1, including a pillar wall.
14. (canceled)
15. (canceled)
16 (proviously presented) The die of slaim 1 subscript the leavester that the second of the second o
16. (previously presented) The die of claim 1, wherein the lower lead-free portion is comprised of copper coated with oxide, chromium or nickel.
17. (canceled)
18. (canceled)

19. (previously presented) The die of claim 1, wherein the upper solder material portion is comprised of:

from about 60 to 70% tin and from about 30 to 40% lead; about 63% tin and 37% lead; about 99% tin and SnAg; or 100% tin.

20. (previously presented) The die of claim 1, wherein the solder material portion is comprised of:

about 63% tin and 37% lead; or 100% tin.

- 21. (previously presented) The die of claim 1, wherein the pillar structures having a total height of from about 60 to 150 $\mu m.$
- 22. (previously presented) The die of claim 1, wherein the pillar structures having a total height of about 100 $\mu m.$
- 23. (original) The die of claim 1, wherein the die is used in Surface Acoustic Wave devices and in MEM devices.

S/N: 10/682,054

24. (currently amended) A die, comprising:

a substrate; and

one or more pillar structures formed over the substrate in a pattern; the one

or more pillar structures having a rectangular shape, a round shape, a ring shape, a

wall-like shape or a spline shape; at least one of the one or more pillar structures

are bi-layer having a lower lead-free portion and a coextensive upper solder

material portion.

5

25. (original) The die of claim 24, wherein the one or more pillar structures have a

rectangular shape with a length of from about 789.0 to 1289.0 µm and a width of

about 289.0 μm.

26. (original) The die of claim 24, wherein the one or more pillar structures have a

rectangular shape with a length of about 789.0 μm and a width of about 289.0 μm.

27. (original) The die of claim 24, wherein the one or more pillar structures have a

rectangular shape with a length of about 1289.0 μm and a width of about 289.0 μm.

S/N: 10/682,054

28. (original) The die of claim 24, wherein the one or more pillar structures have a

rectangular shape and the pillar structures are spaced apart lengthwise by about

500.0 μm center-to-center and by about 211.0 μm end-to-end.

29. (original) The die of claim 24, wherein the one or more pillar structures have a

round shape with a diameter of about 289.0 μm.

30. (original) The die of claim 24, wherein the one or more pillar structures have a

round shape with a diameter of about 289.0 µm; the pillar structures being arranged

at least in part in rows and columns with the adjacent round pillar structures being

spaced apart by about 500.0 μm.

31. (original) The die of claim 24, wherein the pillar structure pattern includes a

series of rows and columns.

32. (previously presented) The die of claim 24, wherein the pillar structure pattern

includes a series of rows and columns; the pillar structures arranged in the series of

rows and columns are spaced apart lengthwise by about 500.0 µm center-to-center

in the columns and are spaced apart about 211.0 µm end-to-end.

33. (original) The die of claim 24, wherein the one or more pillar structures include at least one wall-shaped pillar structure.
at least one wall-shaped pillar structure.
34. (original) The die of claim 24, wherein the one or more pillar structures include
at least one wall-shaped pillar structure forming a square.
35. (original) The die of claim 24, including a pillar wall.
36. (canceled)
37. (canceled)
38. (previously presented) The die of claim 24, wherein the lower lead-free portion
is comprised of copper coated with oxide, chromium or nickel.
39. (canceled)
40. (canceled)
41. (previously presented) The die of claim 24, wherein the upper solder material
portion is comprised of:

from about 60 to 70% tin and from about 30 to 40% lead;

about 63% tin and 37% lead;

about 99% tin and SnAg; or

100%tin.

42. (previously presented) The die of claim 24, wherein the upper solder material portion is comprised of:

about 63% tin and 37% lead; or

100%tin.

43. (previously presented) The die of claim 24, wherein the pillar structures having a total height of from about 60 to 150 μm .

44. (previously presented) The die of claim 24, wherein the pillar structures having a total height of about 100 μm .

45. (original) The die of claim 24, wherein the die is used in Surface Acoustic Wave devices and in MEM devices.

46. (currently amended) A method of forming a die, comprising the steps:

providing a substrate; and

5

S/N: 10/682,054

forming one or more pillar structures over the substrate in a pattern; at least

one of the one or more pillar structures are bi-layer having a lower lead-free portion

and a coextensive upper solder material portion.

47. (original) The method of claim 46, wherein the one or more pillar structures have

a rectangular shape, a round shape, a ring shape, a wall-like shape or a spline shape.

48. (original) The method of claim 46, wherein the one or more pillar structures have

a rectangular shape with a length of from about 789.0 to 1289.0 μm and a width of

about 289.0 μm.

49. (original) The method of claim 46, wherein the one or more pillar structures have

a rectangular shape with a length of about 789.0 μm and a width of about 289.0 μm.

50. (original) The method of claim 46, wherein the one or more pillar structures have

a rectangular shape with a length of about 1289.0 μm and a width of about 289.0 μm

51. (original) The method of claim 46, wherein the one or more pillar structures have

a rectangular shape and the pillar structures are spaced apart lengthwise by about

500.0 μm center-to-center and by about 211.0 μm end-to-end.

S/N: 10/682,054

52. (original) The method of claim 46, wherein the one or more pillar structures have

a round shape with a diameter of about 289.0 μm.

53. (original) The method of claim 46, wherein the one or more pillar structures have

a round shape with a diameter of about 289.0 µm; the pillar structures being

arranged at least in part in rows and columns with the adjacent round pillar

structures being spaced apart by about 500.0 μm.

54. (original) The method of claim 46, wherein the pillar structure pattern includes a

series of rows and columns.

55. (previously presented) The method of claim 46, wherein the pillar structure

pattern includes a series of rows and columns; the pillar structures arranged in the

series of rows and columns are spaced apart lengthwise by about 500.0 µm center-to-

center in the columns and are spaced apart about 211.0 µm end-to-end.

56. (original) The method of claim 46, wherein the one or more pillar structures

include at least one wall-shaped pillar structure.

57. (original) The method of claim 46, wherein the one or more pillar structures

include at least one wall-shaped pillar structure forming a square.

Docket: APS 03 - 002 S/N: 10/682,054 58. (original) The method of claim 46, including a pillar wall. 59. (canceled) 60. (canceled) 61. (previously presented) The method of claim 46, wherein the lower lead-free portion is comprised of copper coated with oxide, chromium or nickel. 62. (canceled) 63. (canceled) 64. (previously presented) The method of claim 46, wherein the upper solder material portion is comprised of: from about 60 to 70% tin and from about 30 to 40% lead;

about 63% tin and 37% lead;

about 99% tin and SnAg; or

100%tin.

S/N: 10/682,054

65. (previously presented) The method of claim 46, wherein the upper solder

material portion is comprised of:

about 63% tin and 37% lead; or

100%tin.

66. (previously presented) The method of claim 46, wherein the pillar structures

having a total height of from about 60 to 150 μm.

67. (previously presented) The method of claim 46, wherein the pillar structures

having a total height of about 100 μm.

68. (original) The method of claim 46, wherein the die formed is used in Surface

Acoustic Wave devices and in MEM devices.

69. (new) The method of claim 1, wherein the lower lead-free portion is comprised of

copper.

70. (new) The method of claim 24, wherein the lower lead-free portion is comprised

of copper.

71. (new) The method of claim 46, wherein the lower lead-free portion is comprised of copper.